

**3 Volt Voltage Variable Attenuator
25 dB, DC-2.5 GHz**

**MAAVSS0006
V1**

Features

- Single Voltage Control: 0 to -3 Volts
- 25 dB Attenuation Range at 0.9 GHz
- Low DC Power Consumption
- Lead-Free SOT-25 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free “Green” Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of AT-255

Description

M/A-COM’s MAAVSS0006 is a GaAs MMIC voltage variable absorptive attenuator in a lead-free SOT-25 surface mount plastic package. The MAAVSS0005 is ideally suited for use where variable attenuation, fine tuning, and very low power consumption are required.

Typical applications include radio, cellular, GPS equipment and automatic gain/level control circuits.

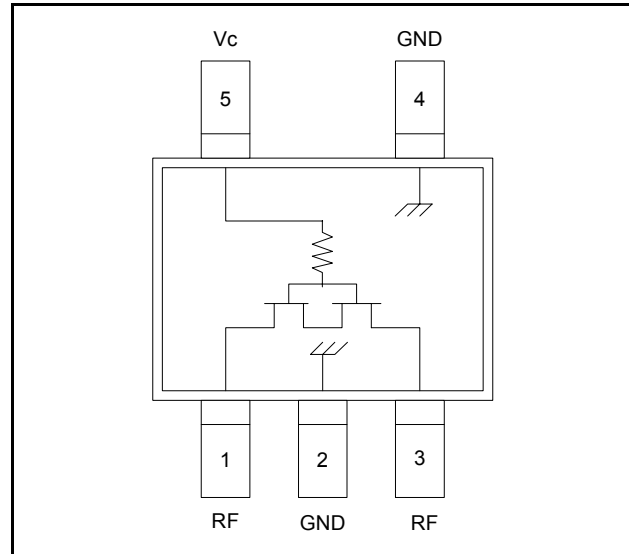
The MAAVSS0006 is fabricated using a mature 1-micron GaAs MESFET process. The process features full chip passivation for increased performance and reliability.

Ordering Information

| Part Number | Package |
|-------------------|-----------------|
| MAAVSS0006 | Bulk Packaging |
| MAAVSS0006TR-3000 | 3000 piece reel |

Note: Reference Application Note M513 for reel size information.

Functional Schematic ¹



1. $V_C = -3\text{ V to }0\text{ V @ }25\text{ }\mu\text{A maximum.}$

Pin Configuration

| Pin No. | Function | Pin No. | Function |
|---------|----------|---------|----------|
| 1 | RF Port | 4 | Ground |
| 2 | Ground | 5 | V_C |
| 3 | RF Port | | |

Absolute Maximum Ratings ^{2,3}

| Parameter | Absolute Maximum |
|-----------------------|---|
| Input Power | +21 dBm |
| Control Voltage V_C | $-8\text{ V} \leq V_C \leq +0.5\text{ V}$ |
| Operating Temperature | $-40^\circ\text{C to }+85^\circ\text{C}$ |
| Storage Temperature | $-65^\circ\text{C to }+150^\circ\text{C}$ |

2. Exceeding any one or combination of these limits may cause permanent damage to this device.
3. M/A-COM does not recommend sustained operation near these survivability limits.

* Restrictions on Hazardous Substances, European Directive 2002/95/EC.

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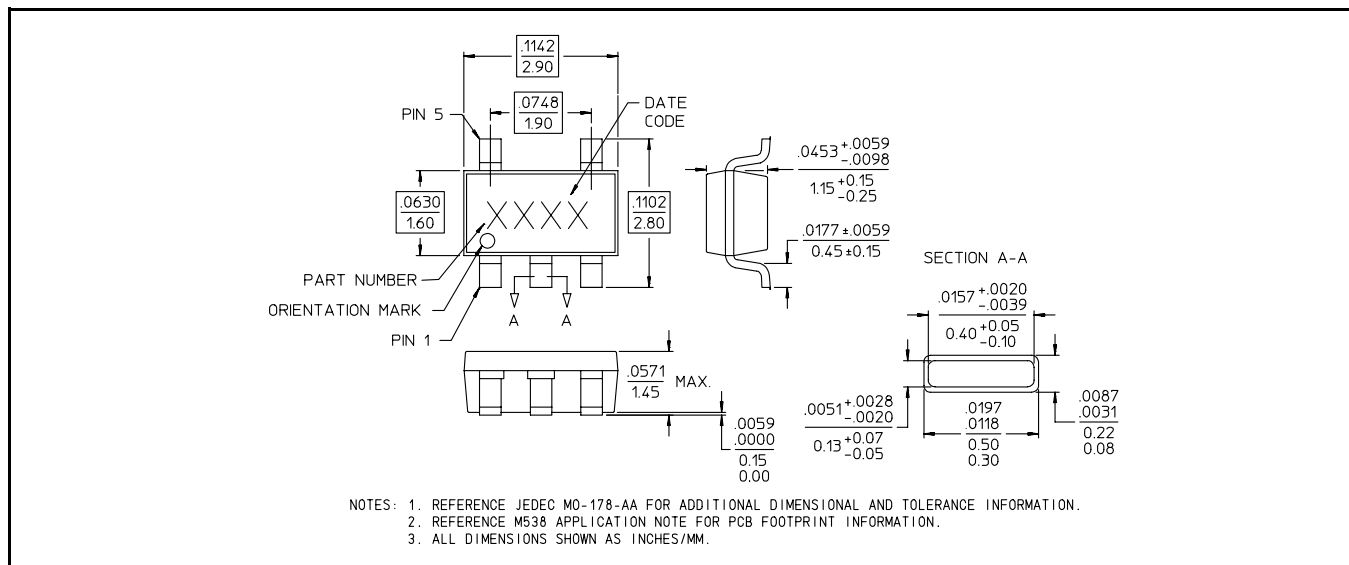
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Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50 \Omega$

| Parameter | Test Conditions | Units | Min | Typ | Max |
|-----------------------------|--|-------|-----|---------|----------|
| Insertion Loss ⁴ | DC - 2.0 GHz | dB | — | 3.6 | 4.2 |
| Attenuation | DC - 1.0 GHz | dB | 23 | 25 | — |
| | 1.0 - 2.0 GHz | dB | 18 | 20 | — |
| Flatness (Peak-to-Peak) | 0.5 - 1.0 GHz | dB | — | ± 7 | ± 10 |
| | 1.0 - 2.0 GHz | dB | — | ± 5 | ± 8 |
| VSWR | DC - 2.0 GHz | Ratio | — | 3:1 | — |
| Trise, Tfall | 10% to 90% RF, 90% to 10% RF | nS | — | 10 | — |
| Ton, Toff | 50% Control to 90% RF, 50% Control to 10% RF | nS | — | 20 | — |
| Transients | In Band | mV | — | 10 | — |

4. Insertion loss varies 0.003 dB/°C.

Lead-Free SOT-25[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

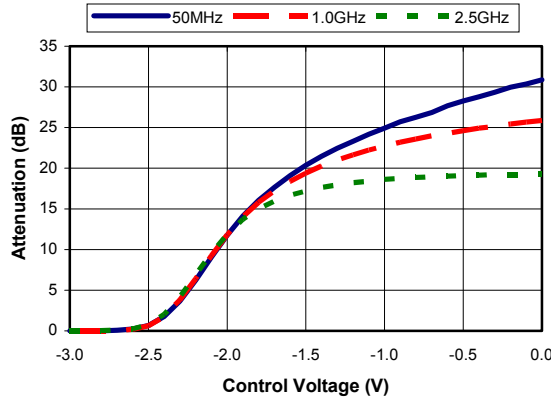
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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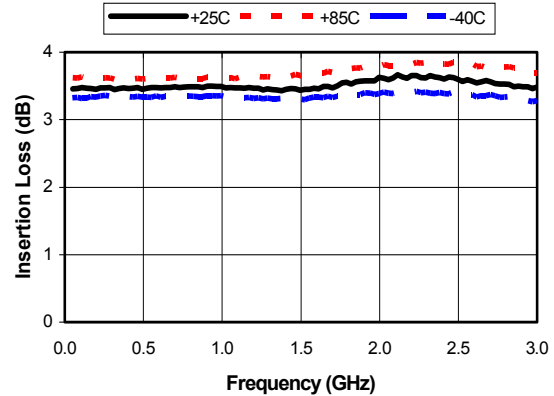
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Typical Performance Curves

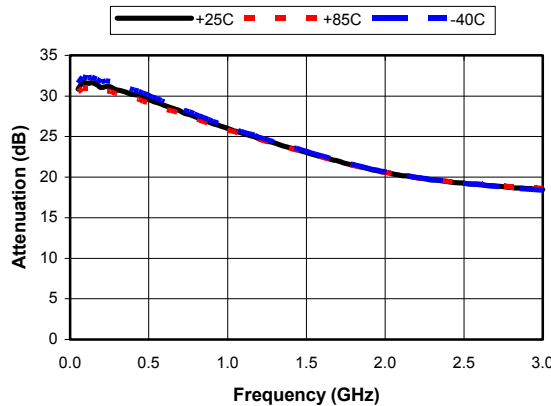
Relative Attenuation vs. Control Voltage



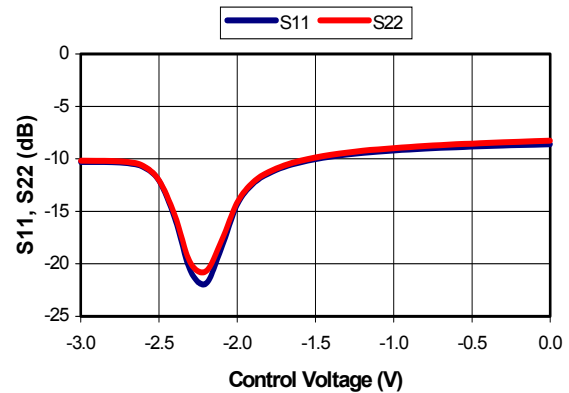
Insertion Loss vs. Frequency



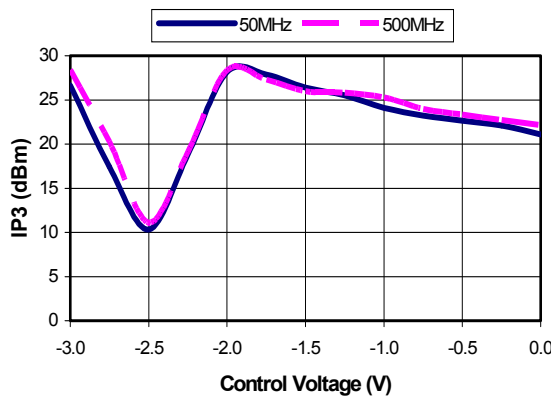
Maximum Relative Attenuation vs. Frequency



Return Loss vs. Control Voltage @ 900 MHz



Input IP3 vs. Control Voltage



Input P1dB vs. Control Voltage

